

Kouichi Murakami

List of Publications by Year in descending order

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84
papers

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citations

331670

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84
docs citations

84
times ranked

935
citing authors

#	ARTICLE	IF	CITATIONS
1	Interaction of Boron and Phosphorus Impurities in Silicon Nanowires during Low-Temperature Ozone Oxidation. Journal of Physical Chemistry C, 2013, 117, 20300-20307.	3.1	22
2	Electron Excitation Memory Induced by Light Irradiation of Hydrogenated Si Nanocrystals Embedded in SiO ₂ . Japanese Journal of Applied Physics, 2013, 52, 115201.	1.5	8
3	Ablation process of PMMA induced by irradiation with laser plasma EUV light. , 2013, , .		0
4	Responses of organic and inorganic materials to intense EUV radiation from laser-produced plasmas. Proceedings of SPIE, 2013, , .	0.8	2
5	Recrystallization and Reactivation of Dopant Atoms in Ion-Implanted Silicon Nanowires. ACS Nano, 2012, 6, 3278-3283.	14.6	22
6	Segregation Behaviors and Radial Distribution of Dopant Atoms in Silicon Nanowires. Nano Letters, 2011, 11, 651-656.	9.1	72
7	Silica ablation process induced by focused laser plasma soft x-rays. , 2011, , .		1
8	Ablation of silica glass induced by laser plasma soft X-ray irradiation. Electronics and Communications in Japan, 2011, 94, 30-35.	0.5	0
9	Microscopic mechanisms behind the high mobility in rubrene single-crystal transistors as revealed by field-induced electron spin resonance. Physical Review B, 2011, 83, .	3.2	64
10	Micromachining Using XUV ^{1/2} X-Ray. The Review of Laser Engineering, 2010, 38, 957-962.	0.0	0
11	Ablation Mechanism of Silica Glass Induced by Laser Plasma Soft X-Rays. The Review of Laser Engineering, 2010, 38, 987-991.	0.0	0
12	Penetration of Hydrogen and Deuterium into Si and Hydrogen States in Si. Journal of the Vacuum Society of Japan, 2010, 53, 265-270.	0.3	0
13	Direct Etching of Poly(methyl methacrylate) Using Laser Plasma Soft X-rays. Applied Physics Express, 2010, 3, 066502.	2.4	9
14	Micromachining of Silica Glass Using EUV Radiation of Laser-Produced Plasma. IEEJ Transactions on Electronics, Information and Systems, 2010, 130, 1779-1783.	0.2	0
15	Nano- and micromachining of transparent materials using laser plasma soft X-rays. , 2009, , .		0
16	Isotope Effect of Penetration of Hydrogen and Deuterium into Silicon through Si/SiO ₂ Interface. Japanese Journal of Applied Physics, 2009, 48, 091204.	1.5	2
17	Electronic States of P Donors in Si Nanocrystals Embedded in Amorphous SiO ₂ Layer Studied by Electron Spin Resonance: Hydrogen Passivation Effects. Japanese Journal of Applied Physics, 2009, 48, 081201.	1.5	4
18	Ablation process of silica glass induced by laser plasma soft X-ray irradiation. Applied Surface Science, 2009, 255, 9840-9842.	6.1	9

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19	Phosphorus ion implantation in silicon nanocrystals embedded in SiO ₂ . Journal of Applied Physics, 2009, 105, .	2.5	23
20	Silica nano-ablation using laser plasma soft x-rays. Proceedings of SPIE, 2009, , .	0.8	0
21	Ablation Process of Silica Glass Induced by Laser Plasma Soft X-ray Irradiation. IEEJ Transactions on Electronics, Information and Systems, 2009, 129, 595-600.	0.2	0
22	Study on Non-Thermal Ablation Process of Silica Glass Using Laser Plasma Soft X-rays toward Nanomachining. IEEJ Transactions on Electronics, Information and Systems, 2009, 129, 1186-1191.	0.2	0
23	Micromachining of inorganic materials using plasma soft x-rays. Electronics and Communications in Japan, 2008, 91, 45-51.	0.5	1
24	Site-selective formation of Si nanocrystal in SiO ₂ by femtosecond laser irradiation and Al deoxidization effects. Applied Physics Letters, 2008, 92, 153112.	3.3	5
25	Ablation of inorganic materials using laser plasma soft X-rays. , 2007, , .		0
26	Direct Nanomachining of Inorganic Transparent Materials Using Laser Plasma Soft X-Rays. Journal of Physics: Conference Series, 2007, 59, 279-284.	0.4	2
27	1.5Åµm light emission of Er ³⁺ ions doped in SiO ₂ films including Si nanocrystallites and in SiO _x films. Journal of Physics: Conference Series, 2007, 59, 466-469.	0.4	0
28	Synthesis of silicon nanocrystals in aluminum-doped SiO ₂ film by laser ablation method. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 31-35.	2.7	5
29	Micromachining of Inorganic Materials using Laser Plasma Soft X-Rays. IEEJ Transactions on Electronics, Information and Systems, 2007, 127, 179-184.	0.2	1
30	First-principle molecular dynamics study of bond disruption and formation in SiO ₂ upon irradiation. Physica B: Condensed Matter, 2006, 376-377, 945-949.	2.7	3
31	Carrier Doping of Silicon Nanowires Synthesized by Laser Ablation. Materials Research Society Symposia Proceedings, 2006, 963, 1.	0.1	0
32	Silica nanomachining using laser plasma soft x rays. Applied Physics Letters, 2006, 89, 101118.	3.3	23
33	Micromachining of inorganic transparent materials using pulsed laser plasma soft x-rays at 10 nm (Invited Paper). , 2005, 5713, 9.		0
34	Free energy molecular dynamics simulations of pulsed-laser-irradiated SiO ₂ : Si- Si bond formation in a matrix of SiO ₂ . Applied Physics Letters, 2005, 86, 201910.	3.3	18
35	Direct micromachining of quartz glass plates using pulsed laser plasma soft x-rays. Applied Physics Letters, 2005, 86, 103111.	3.3	45
36	Laser and Properties of Nanostructured Materials. The Review of Laser Engineering, 2005, 33, 5-11.	0.0	0

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37	Quartz micromachining using laser plasma soft x rays and ultraviolet laser light. Applied Physics Letters, 2004, 85, 1274-1276.	3.3	48
38	Optical excitation of Er ions with 1.5- μ m luminescence via the luminescent state in Si nanocrystallites embedded in SiO ₂ matrices. Applied Physics Letters, 2003, 83, 5422-5424.	3.3	14
39	Hydrogen-terminated defects in ion-implanted silicon probed by monoenergetic positron beams. Journal of Applied Physics, 2003, 93, 3228-3233.	2.5	22
40	Increase of 1.5 μ m luminescence from Cryogenic Temperature to Room Temperature from Er-doped SiO ₂ Films with Si Nanocrystallites Fabricated by Laser Ablation. Japanese Journal of Applied Physics, 2003, 42, 3424-3428.	1.5	11
41	Interaction of Laser Light with Solids. Journal of Plasma and Fusion Research, 2003, 79, 1035-1042.	0.4	5
42	Hyperfine Structure of the Electron Spin Resonance of Phosphorus-Doped Si Nanocrystals. Physical Review Letters, 2002, 89, 206805.	7.8	153
43	Fabrication of Er-doped Si nanocrystallites without thermal quenching of 1.5 μ m photoluminescence. Applied Surface Science, 2002, 197-198, 607-609.	6.1	9
44	<title>Synthesis of silicon nanoparticles and impurity doping by laser ablation</title>. , 2001, , .		0
45	Formation dynamics of silicon nanoparticles after laser ablation studied using plasma emission caused by second-laser decomposition. Applied Physics Letters, 2000, 76, 1401-1403.	3.3	53
46	Synthesis of Functional Nanoparticles by Laser Ablation. The Review of Laser Engineering, 2000, 28, 332-332.	0.0	0
47	Formation Dynamics and Visible Photoluminescence of Silicon Nanoparticles.. The Review of Laser Engineering, 2000, 28, 338-341.	0.0	0
48	Laser-induced Plasma X-ray Source and Its Applications. Time Resolved Measurement of Laser-Ablated Particles by LAPXAS(Laser Plasma Soft X-ray Absorption Spectroscopy).. Hyomen Kagaku, 1999, 20, 180-185.	0.0	0
49	Hydrogen Molecule in Crystalline Silicon Treated with Atomic Hydrogen.. Hyomen Kagaku, 1997, 18, 495-500.	0.0	1
50	Hydrogen Passivation of Donors and Hydrogen States in Heavily Doped n-Type Silicon. Japanese Journal of Applied Physics, 1996, 35, 3937-3941.	1.5	39
51	Sputtering Phenomenon Induced by Laser-Ablated Particles. Japanese Journal of Applied Physics, 1996, 35, 3436-3439.	1.5	1
52	Time-Resolved X-Ray Absorption Spectroscopy for Laser-Ablated Silicon Particles in Xenon Gas. Japanese Journal of Applied Physics, 1996, 35, L735-L737.	1.5	21
53	Light Emission from Nanometer-Sized Silicon Particles Fabricated by the Laser Ablation Method. Japanese Journal of Applied Physics, 1996, 35, 4780-4784.	1.5	118
54	Time-and-Space Resolved X-Ray Absorption Spectroscopy of Laser-Ablated Si Particles. Japanese Journal of Applied Physics, 1994, 33, 2586-2592.	1.5	43

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55	Effects of collision processes between laser-ablated fragments and ambient gases. AIP Conference Proceedings, 1993, , .	0.4	0
56	Laser Solid Phase Epitaxial Growth of Amorphous GaAs.. The Review of Laser Engineering, 1992, 20, 948-954.	0.0	0
57	Hydrogen states probed by electron-spin resonance of phosphorus donors in silicon. Physical Review B, 1991, 44, 3409-3412.	3.2	9
58	Excitation effect on laser ablated particles by second laser irradiation.. The Review of Laser Engineering, 1991, 19, 254-260.	0.0	7
59	Ion implantation effect in high Tc oxide Y1Ba2Cu3Oy. Nuclear Instruments & Methods in Physics Research B, 1990, 46, 284-286.	1.4	0
60	Application of laser plasma X-ray to the study on semiconductors.. The Review of Laser Engineering, 1990, 18, 959-963.	0.0	0
61	Dynamics of laserâ€ablated particles from highTcsuperconductor YBa2Cu3Oy. Applied Physics Letters, 1989, 54, 2716-2718.	3.3	115
62	Solid phase epitaxy of molecular beam deposited amorphous GaAs on Si. Applied Physics Letters, 1989, 54, 2562-2564.	3.3	8
63	Formation of high Tc, superconducting films by laser induced fragments. Nuclear Instruments & Methods in Physics Research B, 1989, 39, 640-643.	1.4	6
64	Motional effects between on-center and off-center substitutional nitrogen in silicon. Physical Review B, 1988, 38, 1589-1592.	3.2	25
65	Electronic Energy Level of Off-Center Substitutional Nitrogen in Silicon: Determination by Electron Spin Resonance Measurements. Japanese Journal of Applied Physics, 1988, 27, L1414-L1416.	1.5	13
66	Y-Ba-Cu Oxide Films Formed with Pulsed-Laser Induced Fragments. Japanese Journal of Applied Physics, 1988, 27, L628-L631.	1.5	17
67	Energy Beam Irradiation of High-TcSuperconductors Y1Ba2Cu3O7-yand Ho1Ba2Cu3O7-y. Japanese Journal of Applied Physics, 1987, 26, L1731-L1733.	1.5	16
68	Explosive crystallization starting from an amorphous-silicon surface region during long pulsed-laser irradiation. Physical Review Letters, 1987, 59, 2203-2206.	7.8	65
69	Chargeâ€state changes of substitutional nitrogen impurities in silicon induced by additional impurities and defects. Journal of Applied Physics, 1987, 61, 4862-4868.	2.5	14
70	Pulsed-laser irradiated silicon studied by time-resolved x-ray absorption (90â€“300 eV). Physical Review Letters, 1986, 56, 655-658.	7.8	59
71	Substitutional nitrogen impurities in pulsedâ€laser annealed silicon. Applied Physics Letters, 1984, 45, 176-178.	3.3	18
72	Timeâ€resolved and spaceâ€resolved Si latticeâ€temperature measurements during cw laser annealing of Si on sapphire. Applied Physics Letters, 1984, 45, 659-661.	3.3	20

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73	Dynamic Behavior of Picosecond and Nanosecond Pulsed Laser Annealing in Ion-Implanted Semiconductors. , 1984, , 171-195.		1
74	Time-resolved optical measurement of Si lattice temperature during nanosecond pulsed laser annealing. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 117-118, 1024-1026.	0.9	5
75	Time-Resolved Si Lattice-Temperature Measurement on Wide Time Scale (10^{-9} ~ 100 sec.) During Laser Annealing. Materials Research Society Symposia Proceedings, 1983, 23, 167.	0.1	0
76	Conductivity Change Due to Electron Spin Resonance in Amorphous Si-Au System. Journal of the Physical Society of Japan, 1981, 50, 1970-1977.	1.6	22
77	Deep levels in implanted, pulse-laser-annealed GaAs. Nuclear Instruments & Methods, 1981, 182-183, 699-703.	1.2	3
78	Measurement of Lattice Temperature during Pulsed-Laser Annealing by Time-Dependent Optical Reflectivity. Japanese Journal of Applied Physics, 1981, 20, L867-L870.	1.5	39
79	Fabrication of non-equilibrium Si: Te and Si: Zn Systems with extremely high impurity concentration by means of laser annealing.. The Review of Laser Engineering, 1981, 9, 434-438.	0.0	0
80	Ultra-Short Pulse Laser Annealing. Materials Research Society Symposia Proceedings, 1980, 1, 97.	0.1	2
81	Dynamic behavior of mode-locked Nd:YAG laser annealing in ion-implanted Si, GaAs, and GaP. Applied Physics Letters, 1979, 35, 628-630.	3.3	14
82	Laser-irradiation effects on unencapsulated GaAs studied by capacitance spectroscopy. Applied Physics Letters, 1979, 35, 156-158.	3.3	14
83	Zeeman energy transfer at the surface layer of P+ ion-implanted silicon. Surface Science, 1979, 86, 655-664.	1.9	0
84	ESR Studies on Defects and Amorphous Phase in Silicon Produced by Ion Implantation. Japanese Journal of Applied Physics, 1973, 12, 1307-1316.	1.5	25